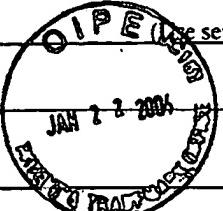


FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office			Attorney Docket Number 5308-156		Serial No. 09/911,995	
<p style="text-align: center;">LIST OF DOCUMENTS CITED BY APPLICANT <i>(If several sheets if necessary)</i></p> <p style="text-align: right;"><i>OCT 1 2003 REC'D. DEPT. OF COMMERCE U.S. PATENT & TRADEMARK OFFICE</i></p>			Applicants: Ryu et al.			
			Filing Date: July 24, 2001		Group: 2811	
			U. S. PATENT DOCUMENTS			
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
<i>RK</i>	1. 5,587,870	12/24/96	Anderson et al.	361	313	
<i>J</i>	2. 5,877,045	3/2/99	Kapoor	438	151	
<i>J</i>	3. 6,136,728	10/24/00	Wang	438	773	
<i>J</i>	4. 6,063,698	05/16/00	Tseng et al.	438	585	
<i>J</i>	5. 6,048,766	04/11/00	Gardner et al.	438	257	
<i>EJM</i>	6. 6,028,012	02/22/00	Wang	438	779	
FOREIGN PATENT DOCUMENTS						
	Document Number	Date	Country	Class	Subclass	Translation Yes No
<i>EJM</i>	7. WO99/63591	12/09/99	PCT			
<i>EJM</i>	8. WO00/13236	03/09/00	PCT			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
<i>EJM</i>	9. Mutin, P. Herbert, "Control of the Composition and Structure of Silicon Oxycarbide and Oxynitride Glasses Derived from Polysiloxane Precursors," <i>Journal of Sol-Gel Science and Technology</i> . Vol. 14 (1999) pp. 27-38.					
<i>EJM</i>	10. del Prado et al. "Full Composition Range Silicon Oxynitride Films Deposited by ECR-PECVD at Room Temperatures," <i>Thin Solid Films</i> . Vol. 343-344 (1999) p. 437-440.					
<i>EJM</i>	11. Wang et al. "High Temperature Characteristics of High-Quality SiC MIS Capacitors with O/N/O Gate Dielectric," <i>IEEE Transactions on Electron Devices</i> . Vol. 47, No. 2, February 2000.					

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U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
<i>Ryu</i>	1	5,479,316	12/26/95	Smrtic et al.	361	322	
	2	5,739,564	04/14/98	Kosa et al.	257	298	
	3	6,228,720	05/08/01	Kitabatake et al.	438	268	
	4	6,239,463	05/29/01	Williams et al.	257	328	
	5	6,316,791	11/13/01	Schörner et al.	257	77	
	6	6,593,620	07/15/03	Hsieh et al.	257	335	
<i>Ryu</i>	7	6,610,366	08/26/03	Lipkin	427	378	
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes No
<i>Ryu</i>	8	WO98/02924	01/22/98	PCT			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
<i>Ryu</i>	9	Dimitrijev et al., "Nitridation of Silicon-Dioxide Films Grown on 6H Silicon Carbide", <i>IEEE Electronic Device Letters</i> , Vol. 18, No. 5, May 05, 1997, pp. 175-177.					
	10	De Mao et al., "Thermal Oxidation of SiC in N ₂ O", <i>J. Electrochem. Soc.</i> , Vol. 141, 1994, pp. L150-L152.					
	11	Ryu et al., Article and Presentation: "27 mΩ-cm ² , 1.6 kV Power DiMOSFETs in 4H-SiC," <i>Proceedings of the 14 International Symposium on Power Semiconductor Devices & ICs 2002</i> , June 4-7, 2002, Santa Fe, NM.					
	12	Kobayashi et al. "Dielectric Breakdown and Current Conduction of Oxide/Nitride/Oxide Multi-Layer Structures," <i>1990 IEEE Symposium on VLSI Technology</i> . pp. 119-120.					
<i>Ryu</i>	13	Ma et al. "Fixed and trapped charges at oxide-nitride-oxide heterostructure interfaces formed by remote plasma enhanced chemical vapor deposition," <i>J. Vac. Sci. Technol. B</i> . Vol. 11, No. 4, Jul/Aug 1993, pp. 1533-40.					

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